

# 6F/6FR

## 6 AMPERE SILICON POWER DIODE



**NAINA**

### SILICON RECTIFIERS 6 AMPERE SILICON POWER DIODES

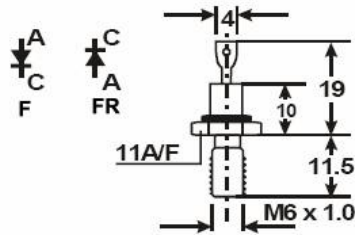
#### FEATURES

- All Diffused Series
- Available in Normal & Reverse Polarity
- Industrial Grade
- Available In Avalanche Characteristic
- \* Available in metric and UNF thread

#### ELECTRICAL SPECIFICATIONS

	6F/FR
$I_{FAV}$	Maximum Average Forward Current $T_c=150^\circ\text{C}$ 6A
V <sub>FM</sub>	Maximum peak forward voltage drop @ Rated $I_F$ 1.2 V
$I_{FSM}$	Maximum peak one cycle (non-rep) surge current 10 m sec 175 A
$I_{FRM}$	Maximum peak repetitive surge current 30 A
$I^2t$	Maximum $I^2t$ rating (non-rep.) for 5 to 10 m sec. 150A <sup>2</sup> sec

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#### THERMAL MECHANICAL SPECIFICATIONS

$\theta_{JC}$	Maximum thermal resistance Junction to case	2.5°C/W
$T_j$	Operating Junction Temp.	-65°C to 150°C
$T_{stg}$	Storage temperature	-65°C to 150°C
	Mounting torque (non-lubricated threads)	0.14mkg min, 0.17mkg max
W	Approx, weight	7 gms.

#### ELECTRICAL RATINGS

TYPE	NUMBER 6F/FR	10	20	40	60	80	100	120	140	160
V <sub>RRM</sub>	Max. repetitive peak reverse voltage (v)	100	200	400	600	800	1000	1200	1400	1600
V <sub>R(RMS)</sub>	Max. R.M.S. reverse voltage (V)	70	140	280	420	560	700	840	980	1120
V <sub>R</sub>	Max. D.C. Blocking Voltage (V)	100	200	400	600	800	1000	1200	1400	1600
	Recommended R.M.S. working Voltage(v)	40	80	160	240	320	400	480	560	640
I <sub>R(AV)</sub>	Max. Average reverse leakage current @ V <sub>RRM</sub> T <sub>c</sub> 25°C uA	100	100	100	100	100	100	100	100	100

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